

PRELIMINARY

Data Sheet

January 1999

File Number

4647

Low Power Quad RS-232 Receiver

The HIN14C89E is a high-ESD tolerant, very low power, quad RS-232 receiver interface circuit that is designed to meet EIA/TIA-232, EIA/TIA-562, and CCITT V.28 specifications.

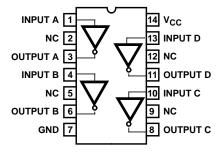
The receivers can handle up to ± 25 V, and have a 3 to 7k Ω input impedance. The receivers have hysteresis and on-chip noise filtering to improve noise rejection and make external filtering components unnecessary. The outputs are TTL and CMOS compatible and operate at 240Kbps.

Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
HIN14C89ECP	0 to 70	14 Ld PDIP	E14.3
HIN14C89ECBN	0 to +70	14 Ld SOIC	M14.15

Pinout

HIN14C89E (PDIP, SOIC) TOP VIEW



Features

- Pin-Compatible ESD Upgrade for "1489" Socket
- · Meets All RS-232C Specifications
- · Enhanced ESD Protection
 - ±15KV Human Body Model
 - ±15KV IEC1000-4-2, Air-Gap Discharge
 - ±8KV IEC1000-4-2, Contact Discharge
- · Latch-Up Free During an ESD Event
- Very Low Power Consumption (1μA Typical)
- 240Kbps Data Rate (Typical)
- · 4 Receivers per Package
 - ±25V Input Voltage Range
 - 3 to 7kΩ Input Impedance
 - 0.5V Hysteresis to Improve Noise Rejection
- All Critical Parameters are Guaranteed Over the Entire Commercial Temperature Range
 - Functionally Interchangeable and Pin Compatible with MAX1489E, MC1489, MC14C89A, SN75189, SN75C189, DS1489, DS14C89, and DS14C89A

Applications

- · Computers Portable and Mainframe
- Peripherals Printers and Terminals
- Modems
- Dataloggers

HIN14C89E

Absolute Maximum Ratings

V_{CC} to Ground
Input A - D
Output Voltages
Output A - D (GND -0.3V) $<$ VRXOUT $<$ (V+ +0.3V)
Short Circuit Duration
Output A - D
Continuous Total Power Dissipation (T _A = 25°C)
Plastic Package
Derate -7.0 mW/C above 70°C
ESD Classification: EIC1000-4-2 Class 4 Compliant

Thermal Information

Thermal Resistance (Typical, Note 1)	θ_{JA} (°C/W)
14 Ld PDIP Package	90
14 Ld SOIC Package	
Maximum Junction Temperature (Plastic Package)	
Maximum Storage Temperature Range65	^o C to 150 ^o C
Maximum Lead Temperature (Soldering 10s)	300°C
Temperature Ranges	
HIN14C89EC	0°C to 70°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

Electrical Specifications Test Conditions: V_{CC} = +5 V_{CC} =

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Output Voltage High, V _{OH}	I _{OUT} = -3.2mA	2.5	4.1	-	V
Output Voltage Low, V _{OL}	I _{OUT} = 3.2mA	-	0.17	0.4	V
Output Short Circuit Current, IOS	Shorted to GND	-	-11	-	
(Note 2)	Shorted to V _{CC}	-	35	-	mA
Supply Current, I _{CC}		-	1	100	μΑ
Input Voltage Range, V _{IN}		-25	-	25	V
Input Voltage High, V _{IH}		-	2.15	2.60	V
Input Voltage Low, V _{IL}		0.75	1.4	-	V
Input Hysteresis, V _{HYST}		-	0.7	-	V
Input Resistance, R _{IN}		3.0	5.0	7.0	kΩ
Output Propagation Delay, Low to High, t _{PLH}		-	1.9	4.0	μS
Output Propagation Delay, High to Low, t _{PHL}		-	2.0	4.0	μS
Output Propagation Delay Skew, [t _{PLH} + t _{PHL}], t _{SKEW}		-	120	-	nS
Output Transition Time, t _{TR}	V _{OUT} = 10% to 90%	-	110	-	nS
Input Noise Rejection, t _N	Pulse Amplitude = 5V	-	0.8	-	μS
Guaranteed Data Rate, DR	V _{CC} = 5V	120	240	-	kbps
ESD Protection	Human Body Model (Note 3) IEC1000-4-2 (Contact Discharge) IEC1000-4-2 (Air-Gap Discharge)	-	±15 ±8 ±15	-	kV

NOTES:

- 2. Guaranteed by design.
- 3. R_{IN} pins to GND.

Pin Description

PIN	NAME	FUNCTION
1, 4, 10, 13	INPUT	Receiver Inputs
2, 5, 9, 12	N.C.	No Connects
3, 6, 8, 11	OUTPUT	Receiver Outputs
7	GND	Ground
14	V _{CC}	Supply Voltage

Timing Diagram

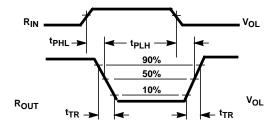


FIGURE 1. PROPAGATION DELAY DEFINITION

HIN14C89E

Die Characteristics

DIE DIMENSIONS:

67 x 76 x 14 ±1 mils

METALLIZATION:

Type: Al

Thickness: 10kÅ ±1kÅ

PASSIVATION:

Type: SiO₂ / Si₃N₄ Sandwich

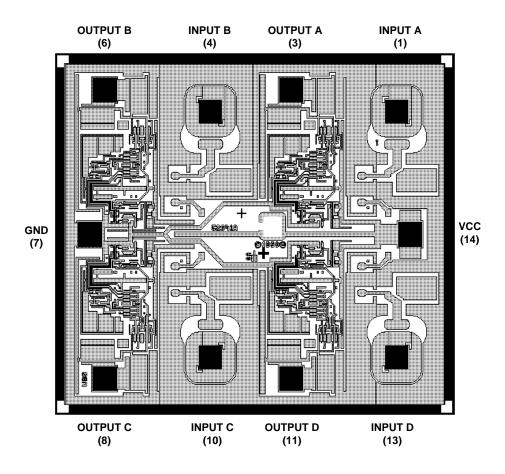
Thickness: 7kÅ ±20% Oxide under 8kÅ ±15% Nitride

WORST CASE CURRENT DENSITY:

 $2.2 \times 10^4 \text{ A/cm}^2$

Metallization Mask Layout

HIN14C89E



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